

**• General Description**

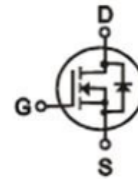
It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

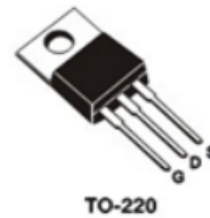
- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

• Product Summary

$V_{DS} = 40V$

$R_{DS(ON)} = 1.8m\Omega$

$I_D = 178A$

**• Ordering Information:**

Part NO.	ZMS018N04P
Marking	ZMS018N04
Packing Information	TUBE
Basic ordering unit (pcs)	1000

• Absolute Maximum Ratings ($T_C=25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D @ T_C=25^\circ C$	178	A
	$I_D @ T_C=75^\circ C$	135	A
	$I_D @ T_C=100^\circ C$	112	A
Pulsed Drain Current ①	I_{DM}	534	A
Total Power Dissipation	$P_D @ T_C=25^\circ C$	113	W
Total Power Dissipation	$P_D @ T_A=25^\circ C$	3.2	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	210	mJ



•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	1.1	$^{\circ}C/W$
Thermal resistance, junction - ambient	R_{thJA}	-	-	35	$^{\circ}C/W$
Soldering temperature, wave soldering for 10s	T_{sold}	-	-	265	$^{\circ}C$

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	40			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.2		2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 40V, V_{GS} = 0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 24A$		1.8	2.0	$m\Omega$
		$V_{GS} = 4.5V, I_D = 12A$		2.9	3.6	$m\Omega$
Forward Transconductance	g_{FS}	$V_{DS} = 25V, I_D = 20A$		22		s
Source-drain voltage	V_{SD}	$I_S = 24A$			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$f = 1MHz$	-	2250	-	pF
Output capacitance	C_{oss}		-	620	-	
Reverse transfer capacitance	C_{rss}		-	46	-	

•Gate Charge characteristics($T_a = 25^{\circ}C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 25V$ $I_D = 8A$ $V_{GS} = 10V$	-	41	-	nC
Gate - Source charge	Q_{gs}		-	6.5	-	
Gate - Drain charge	Q_{gd}		-	11.8	-	

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;



Fig.1 Power Dissipation

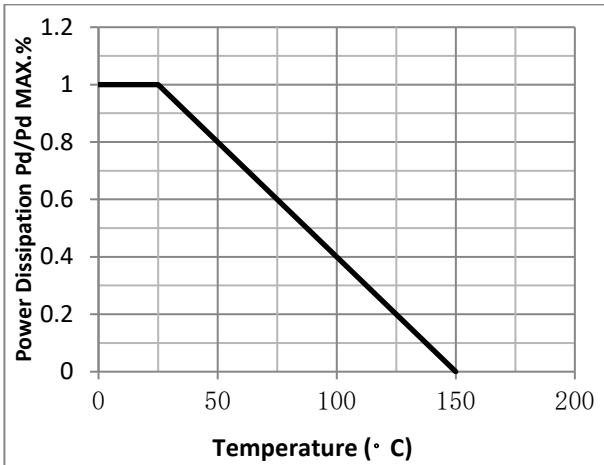


Fig.2 Typical output Characteristics

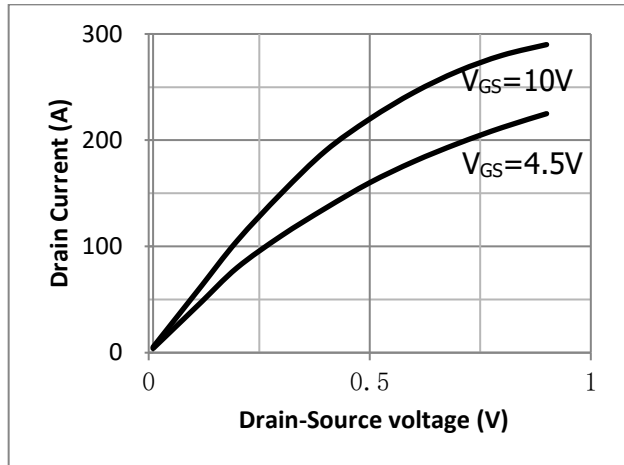


Fig.3 Threshold Voltage V.S Junction Temperature

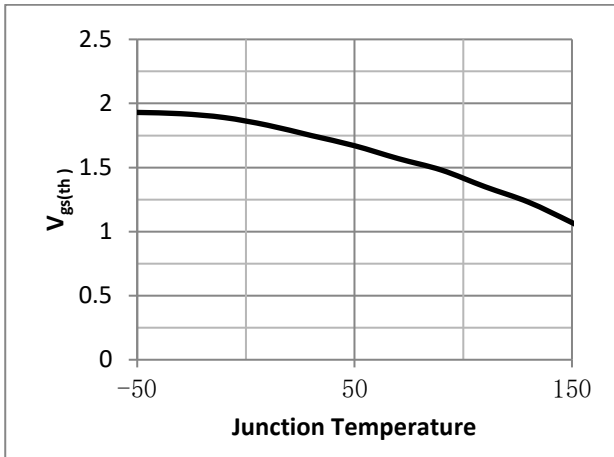


Fig.4 Resistance V.S Drain Current

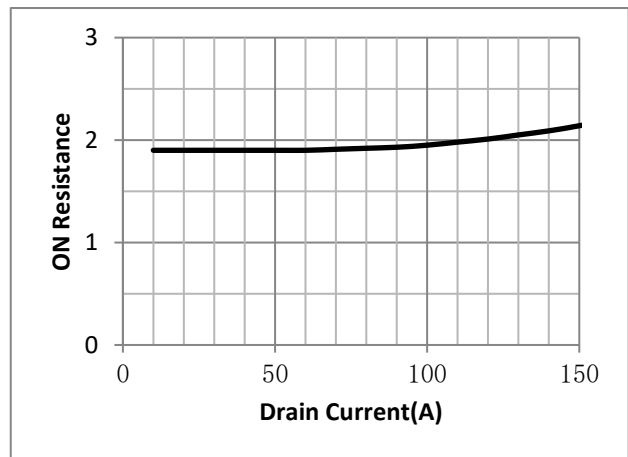


Fig.5 On-Resistance VS Gate Source Voltage

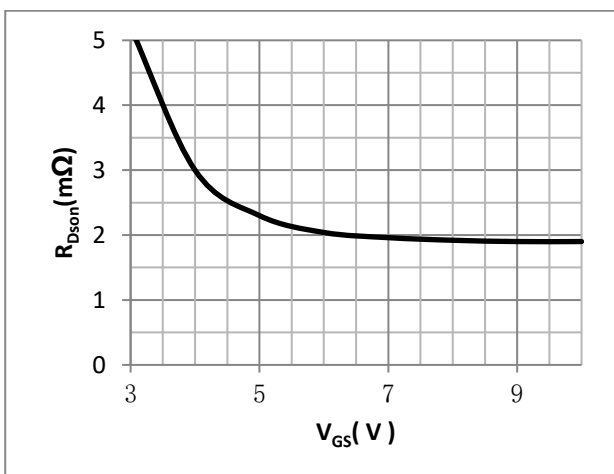


Fig.6 On-Resistance V.S Junction Temperature

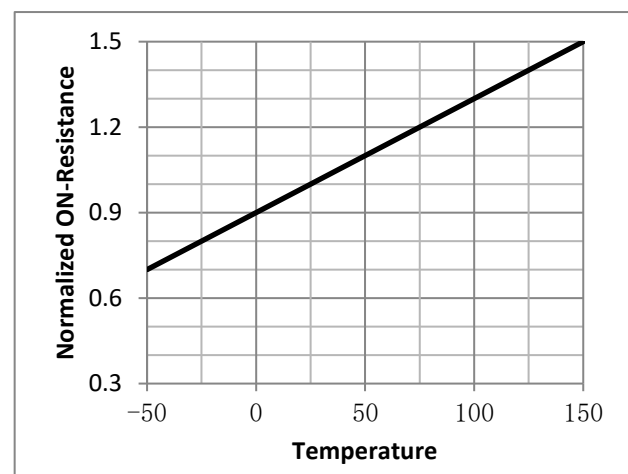




Fig.7 Gate Charge Characteristics

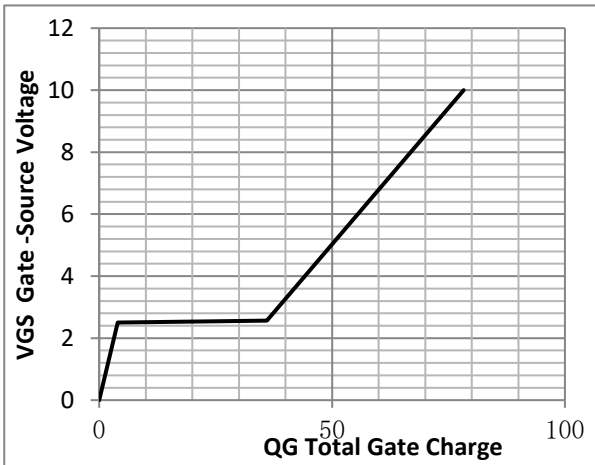


Fig.8 Capacitance vs Vds

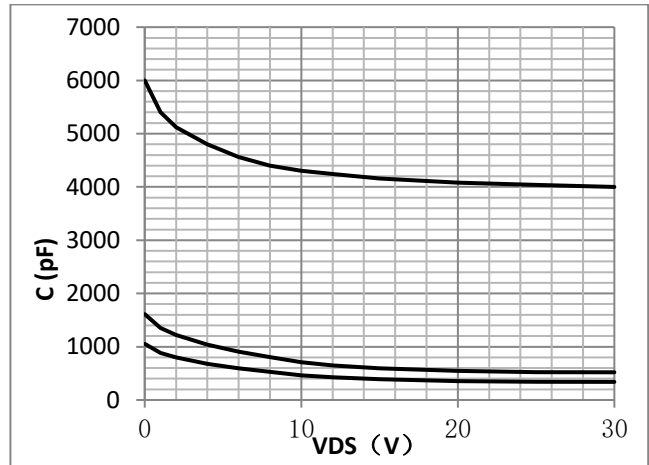


Fig.9 SOA Maximum Safe Operating Area

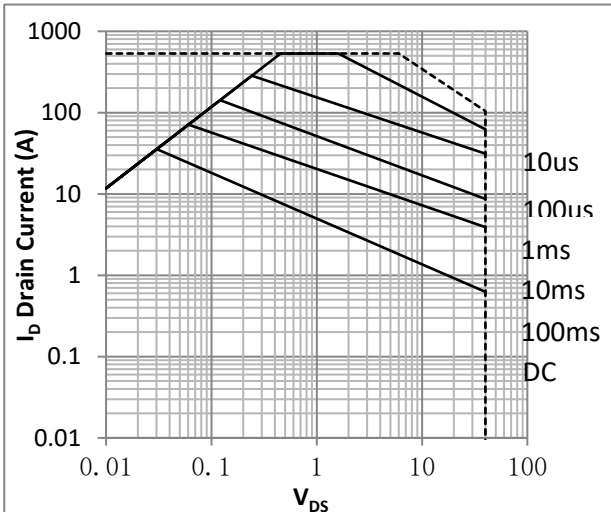


Fig.10 ID-Junction Temperature

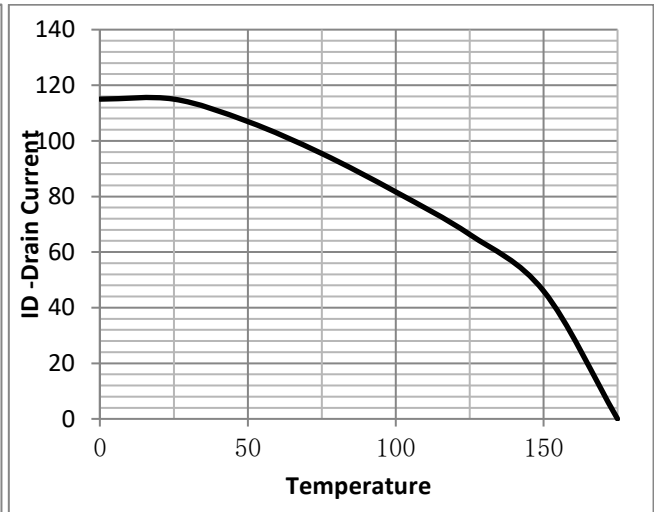


Fig.11 Switching Time Measurement Circuit

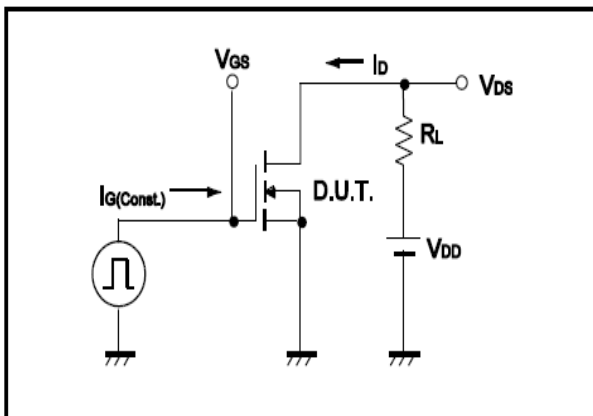


Fig.12 Gate Charge Waveform

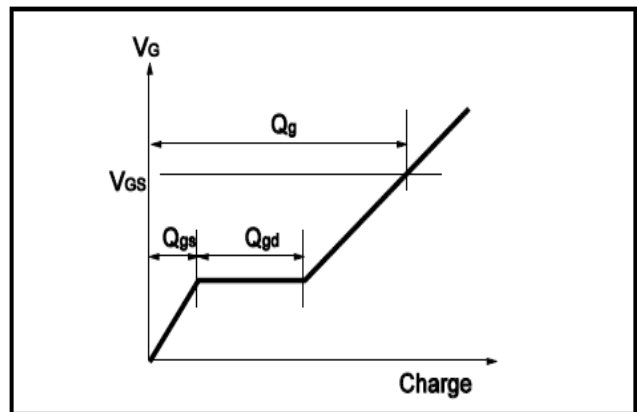




Fig.13 Resistive Switching Test Circuit

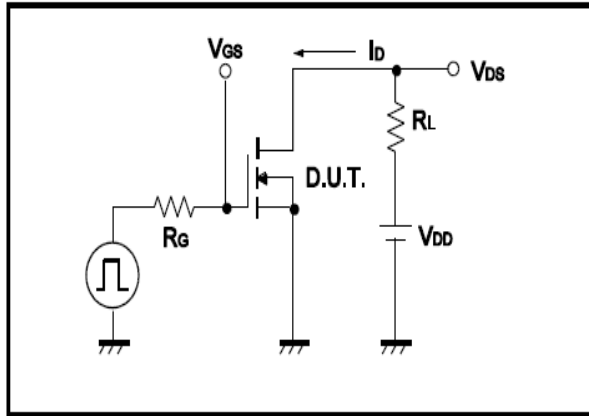


Fig.14 Resistive Switching Test Waveform

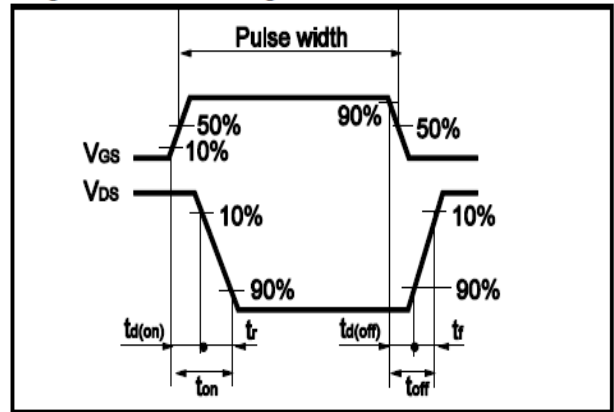


Fig.15 Avalanche Measurement Circuit

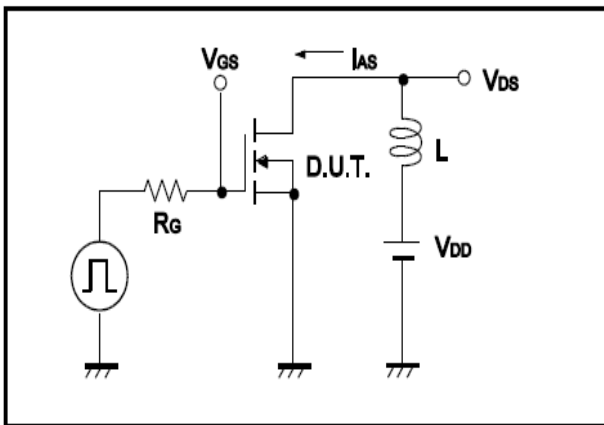
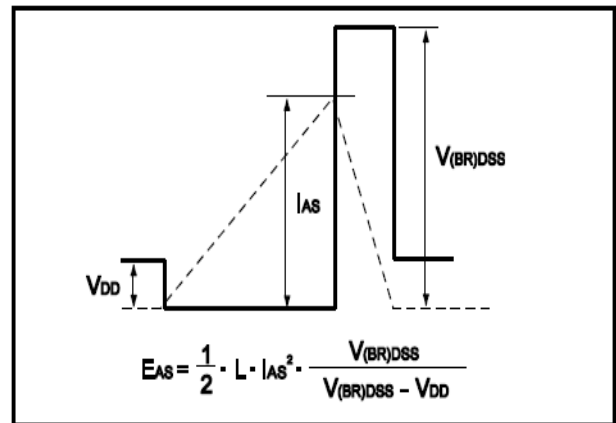


Fig.16 Avalanche Waveform





•Dimensions (TO-220)

Unit: mm

SYMBOL	min	nom	max	SYMBOL	min	nom	max
A	4.00		4.80	E	9.90		10.70
B	1.10		1.40	e		2.54	
B1	1.10		1.40	F	1.10		1.45
b1	0.65		1.00	L	12.50		14.50
c	0.35		0.75	L1	3.00	3.50	4.00
D	15.00		16.50	Q	2.50		3.00
D1	5.90		6.90	Q1	2.00		3.00
				ΦP	3.60		3.90

